## FEATURES

1.8 V to 5.5 V single supply
$2 \Omega$ (typical) on resistance
Low on resistance flatness
-3 dB bandwidth > 200 MHz
Rail-to-rail operation
Fast switching times
ton 18 ns
toff 12 ns
Typical power consumption < $0.01 \mu \mathrm{~W}$
TTL/CMOS-compatible

## APPLICATIONS

Battery-powered systems
Communications systems
Sample-and-hold systems
Audio signal routing
Video switching
Mechanical reed relay replacement

## GENERAL DESCRIPTION

The ADG701/ADG702 are monolithic CMOS SPST switches. These switches are designed on an advanced submicron process that provides low power dissipation yet high switching speed, low on resistance, and low leakage currents. In addition, -3 dB bandwidths of greater than 200 MHz can be achieved.

The ADG701/ADG702 can operate from a single 1.8 V to 5.5 V supply, making it ideal for use in battery-powered instruments and with the new generation of DACs and ADCs from Analog Devices, Inc.

Figure 1 shows that with a logic input of 1 , the switch of the ADG701 is closed and that of the ADG702 is open. Each switch conducts equally well in both directions when on.

The ADG701/ADG702 are available in 5-lead SOT-23, 6-lead SOT-23, and 8-lead MSOP packages.

## FUNCTIONAL BLOCK DIAGRAM



SWITCHES SHOWN FOR A LOGIC 1 INPUT
Figure 1.

## PRODUCT HIGHLIGHTS

1. 1.8 V to 5.5 V Single-Supply Operation. The ADG701/ADG702 offer high performance, including low on resistance and fast switching times, and are fully specified and guaranteed with 3 V and 5 V supply rails.
2. Very Low Ron ( $3 \Omega$ Maximum at $5 \mathrm{~V}, 5 \Omega$ Maximum at 3 V ). At 1.8 V operation, $\mathrm{R}_{\mathrm{ON}}$ is typically $40 \Omega$ over the temperature range.
3. On Resistance Flatness $\mathrm{R}_{\mathrm{FLAT}(\mathrm{ON})}(1 \Omega$ Maximum).
4. -3 dB Bandwidth $>200 \mathrm{MHz}$.
5. Low Power Dissipation.

CMOS construction ensures low power dissipation.
6. Fast $\mathrm{t}_{\mathrm{on}} / \mathrm{t}_{\text {off }}$.

Table 1. Related Devices

| Part No. | Description |
| :--- | :--- |
| ADG701L/ADG702L | Low voltage $2 \Omega$ SPST switches <br> with guaranteed leakage <br> specifications |

## ADG701/ADG702

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## SPECIFICATIONS

$\mathrm{V}_{\mathrm{DD}}=5 \mathrm{~V} \pm 10 \%$, GND $=0 \mathrm{~V}$. Temperature range for B version is $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$, unless otherwise noted.
Table 2.

| Parameter | $+25^{\circ} \mathrm{C}$ | $\begin{aligned} & \text { sion } \\ & -40^{\circ} \mathrm{C} \text { to } \\ & +85^{\circ} \mathrm{C} \end{aligned}$ | Unit | Test Conditions/Comments |
| :---: | :---: | :---: | :---: | :---: |
| ANALOG SWITCH <br> Analog Signal Range On Resistance (Ron) <br> On Resistance Flatness (Rflat(on) | $\begin{aligned} & 2 \\ & 3 \\ & 0.5 \end{aligned}$ | 0 V to $\mathrm{V}_{\mathrm{DD}}$ <br> 4 <br> 1.0 | V <br> $\Omega$ typ <br> $\Omega$ max <br> $\Omega$ typ <br> $\Omega$ max | $\begin{aligned} & V_{S}=0 \mathrm{~V} \text { to } \mathrm{V}_{\mathrm{DD}}, \mathrm{I}_{\mathrm{S}}=-10 \mathrm{~mA} ; \text { Figure } 11 \\ & \mathrm{~V}_{\mathrm{S}}=0 \mathrm{~V} \text { to } \mathrm{V}_{\mathrm{DD}}, \mathrm{I}_{\mathrm{S}}=-10 \mathrm{~mA} \end{aligned}$ |
| LEAKAGE CURRENTS <br> Source OFF Leakage, Is (OFF) <br> Drain OFF Leakage, $I_{D}$ (OFF) <br> Channel ON Leakage, $\mathrm{I}_{\mathrm{D}}, \mathrm{I}_{\mathrm{S}}(\mathrm{ON})$ | $\begin{aligned} & \pm 0.01 \\ & \pm 0.01 \\ & \pm 0.01 \end{aligned}$ |  | nA typ nA typ nA typ | $\begin{aligned} & \mathrm{V}_{\mathrm{DD}}=5.5 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{S}}=4.5 \mathrm{~V} / 1 \mathrm{~V}, \mathrm{~V}_{\mathrm{D}}=1 \mathrm{~V} / 4.5 \mathrm{~V} \text {; Figure } 12 \\ & \mathrm{~V}_{\mathrm{S}}=4.5 \mathrm{~V} / 1 \mathrm{~V}, \mathrm{~V}_{\mathrm{D}}=1 \mathrm{~V} / 4.5 \mathrm{~V} \text {; Figure } 12 \\ & \mathrm{~V}_{\mathrm{S}}=\mathrm{V}_{\mathrm{D}}=1 \mathrm{~V} \text {, or } 4.5 \mathrm{~V} \text {; Figure } 13 \end{aligned}$ |
| DIGITAL INPUTS <br> Input High Voltage, Vinh Input Low Voltage, VINL Input Current linl or linh | $0.005$ | 2.4 <br> 0.8 <br> $\pm 0.1$ | $V$ min <br> V max <br> $\mu \mathrm{A}$ typ <br> $\mu \mathrm{A}$ max | $\mathrm{V}_{\text {IN }}=\mathrm{V}_{\text {INL }}$ or $\mathrm{V}_{\text {INH }}$ |
| DYNAMIC CHARACTERISTICS ${ }^{1}$ <br> ton <br> toff <br> Charge Injection <br> Off Isolation <br> Bandwidth -3 dB <br> $\mathrm{C}_{\mathrm{s}}$ (OFF) <br> $\mathrm{C}_{\mathrm{D}}$ (OFF) <br> $\mathrm{C}_{\mathrm{D}}, \mathrm{C}_{\mathrm{S}}(\mathrm{ON})$ | $\begin{aligned} & 12 \\ & 8 \\ & 5 \\ & 5 \\ & -55 \\ & -75 \\ & 200 \\ & 17 \\ & 17 \\ & 38 \\ & \hline \end{aligned}$ | 18 12 | ns typ ns max ns typ ns max pC typ dB typ dB typ MHz typ pF typ pF typ pF typ | $\begin{aligned} & \mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} \\ & \mathrm{~V}_{\mathrm{S}}=3 \mathrm{~V} ; \text { Figure } 14 \\ & \mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} \\ & \mathrm{~V}_{\mathrm{S}}=3 \mathrm{~V} ; \text { Figure } 14 \\ & \mathrm{~V}_{\mathrm{S}}=2 \mathrm{~V}, \mathrm{R}_{\mathrm{S}}=0 \Omega, \mathrm{C}_{\mathrm{L}}=1 \mathrm{nF} ; \text { Figure } 15 \\ & \mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}, \mathrm{f}=10 \mathrm{MHz} \\ & \mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}, \mathrm{f}=1 \mathrm{MHz} ; \text { Figure } 16 \\ & \mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF} ; \text { Figure } 17 \end{aligned}$ |
| POWER REQUIREMENTS IDD | 0.001 | 1.0 | $\mu \mathrm{A}$ typ <br> $\mu \mathrm{A}$ max | $\begin{aligned} & \hline \mathrm{V}_{\mathrm{DD}}=5.5 \mathrm{~V} \\ & \text { Digital inputs }=0 \mathrm{~V} \text { or } 5 \mathrm{~V} \end{aligned}$ |

[^0]
## ADG701/ADG702

$\mathrm{V}_{\mathrm{DD}}=3 \mathrm{~V} \pm 10 \%$, GND $=0 \mathrm{~V}$. Temperature range for B version is $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$, unless otherwise noted.
Table 3.

| Parameter | $+25^{\circ} \mathrm{C}$ | $\begin{aligned} & \text { sion } \\ & -40^{\circ} \mathrm{C} \text { to } \\ & +85^{\circ} \mathrm{C} \end{aligned}$ | Unit | Test Conditions/Comments |
| :---: | :---: | :---: | :---: | :---: |
| ANALOG SWITCH <br> Analog Signal Range On Resistance (Ron) <br> On Resistance Flatness (Relation) | $\begin{aligned} & 3.5 \\ & 5 \\ & 1.5 \end{aligned}$ | 0 V to $\mathrm{V}_{\mathrm{DD}}$ <br> 6 | V <br> $\Omega$ typ <br> $\Omega$ max <br> $\Omega$ typ | $\begin{aligned} & V_{S}=0 \mathrm{~V} \text { to } \mathrm{V}_{\mathrm{DD}}, \mathrm{I}_{\mathrm{S}}=-10 \mathrm{~mA} \text {; Figure } 11 \\ & \mathrm{~V}_{\mathrm{S}}=0 \mathrm{~V} \text { to } \mathrm{V}_{\mathrm{DD}}, \mathrm{I}_{\mathrm{S}}=-10 \mathrm{~mA} \end{aligned}$ |
| LEAKAGE CURRENTS <br> Source OFF Leakage Is (OFF) <br> Drain OFF Leakage $\mathrm{I}_{\mathrm{D}}$ (OFF) <br> Channel ON Leakage $I_{D}, I_{S}(O N)$ | $\begin{aligned} & \pm 0.01 \\ & \pm 0.01 \\ & \pm 0.01 \\ & \hline \end{aligned}$ |  | nA typ nA typ nA typ | $\begin{aligned} & \mathrm{V}_{\mathrm{DD}}=3.3 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{S}}=3 \mathrm{~V} / 1 \mathrm{~V}, \mathrm{~V}_{\mathrm{D}}=1 \mathrm{~V} / 3 \mathrm{~V} \text {; Figure } 12 \\ & \mathrm{~V}_{\mathrm{S}}=3 \mathrm{~V} / 1 \mathrm{~V}, \mathrm{~V}_{\mathrm{D}}=1 \mathrm{~V} / 3 \mathrm{~V} \text {; Figure } 12 \\ & \mathrm{~V}=\mathrm{V}_{\mathrm{D}}=1 \mathrm{~V} \text {, or } 3 \mathrm{~V} \text {; Figure } 13 \end{aligned}$ |
| DIGITAL INPUTS Input High Voltage, $\mathrm{V}_{\mathrm{INH}}$ Input Low Voltage, VIIL Input Current linl or $l_{\text {INH }}$ | 0.005 | $\begin{aligned} & 2.0 \\ & 0.4 \end{aligned}$ $\pm 0.1$ | $\vee$ min <br> V max <br> $\mu \mathrm{A}$ typ <br> $\mu \mathrm{A}$ max | $\mathrm{V}_{\text {IN }}=\mathrm{V}_{\text {INL }}$ or $\mathrm{V}_{\text {INH }}$ |
| DYNAMIC CHARACTERISTICS ${ }^{1}$ <br> ton <br> toff <br> Charge Injection <br> Off Isolation <br> Bandwidth -3 dB <br> $\mathrm{C}_{\mathrm{s}}$ (OFF) <br> $\mathrm{C}_{\mathrm{D}}$ (OFF) <br> $\mathrm{C}_{\mathrm{D}}, \mathrm{C}_{\mathrm{S}}(\mathrm{ON})$ | 14 <br> 8 <br> 4 <br> -55 <br> -75 <br> 200 <br> 17 <br> 17 <br> 38 | 20 13 | ns typ ns max ns typ ns max pC typ dB typ dB typ MHz typ pF typ pF typ pF typ | $\begin{aligned} & \mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} \\ & \mathrm{~V}_{\mathrm{S}}=2 \mathrm{~V}, \text { Figure } 14 \\ & \mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} \\ & \mathrm{~V}_{\mathrm{S}}=2 \mathrm{~V}, \text { Figure } 14 \\ & \mathrm{~V}_{\mathrm{S}}=1.5 \mathrm{~V}, \mathrm{R}_{\mathrm{S}}=0 \Omega, \mathrm{C}_{\mathrm{L}}=1 \mathrm{nF} ; \text { Figure } 15 \\ & \mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}, \mathrm{f}=10 \mathrm{MHz} \\ & \mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}, \mathrm{f}=1 \mathrm{MHz} \text {; Figure } 16 \\ & \mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF} ; \text { Figure } 17 \end{aligned}$ |
| POWER REQUIREMENTS IDD | 0.001 | 1.0 | $\mu \mathrm{A}$ typ $\mu \mathrm{A}$ max | $\begin{aligned} & \mathrm{V} \mathrm{VD}=3.3 \mathrm{~V} \\ & \text { Digital inputs }=0 \mathrm{~V} \text { or } 3 \mathrm{~V} \end{aligned}$ |

[^1]
## ABSOLUTE MAXIMUM RATINGS

$\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$, unless otherwise noted.
Table 4.

| Parameter | Rating |
| :---: | :---: |
| $V_{\text {DD }}$ to GND | -0.3 V to +7 V |
| Analog and Digital Inputs ${ }^{1}$ | $-0.3 \mathrm{~V} \text { to } \mathrm{V}_{\mathrm{DD}}+0.3 \mathrm{~V}$ <br> or 30 mA , whichever occurs first |
| Continuous Current, S or D | 30 mA |
| Peak Current, S or D | 100 mA , pulsed at 1 ms , $10 \%$ duty cycle maximum |
| Operating Temperature Range Industrial (B Version) | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $-65^{\circ} \mathrm{C}$ to $+150^{\circ} \mathrm{C}$ |
| Junction Temperature | $150^{\circ} \mathrm{C}$ |
| MSOP Package, Power Dissipation | 315 mW |
| $\theta_{\mathrm{jA}}$ Thermal Impedance | $206^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\theta_{\text {jc }}$ Thermal Impedance | $44^{\circ} \mathrm{C} / \mathrm{W}$ |
| SOT-23 Package, Power Dissipation | 282 mW |
| $\theta_{\mathrm{JA}}$ Thermal Impedance | $229.6^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\theta_{\text {¢ }}$ Thermal Impedance | $91.99^{\circ} \mathrm{C} / \mathrm{W}$ |
| Lead Temperature, Soldering |  |
| Vapor Phase ( 60 sec ) | $215^{\circ} \mathrm{C}$ |
| Infrared (15 sec) | $220^{\circ} \mathrm{C}$ |
| Pb-free Reflow Soldering |  |
| Peak Temperature | 260(+0/-5) ${ }^{\circ} \mathrm{C}$ |
| Time at Peak Temperature | 10 sec to 40 sec |
| ESD | 2 kV |

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Only one absolute maximum rating may be applied at any one time.

Table 5. Truth Table

| ADG701 In | ADG702 In | Switch Condition |
| :--- | :--- | :--- |
| 0 | 1 | Off |
| 1 | 0 | On |

[^2]
## ESD CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although this product features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.


## ADG701/ADG702

## PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS



Figure 2. 8-Lead MSOP


Figure 3. 6-Lead SOT-23


Figure 4. 5-Lead SOT-23

Table 6. Pin Descriptions

| Pin No. |  |  |  |  |
| :--- | :--- | :--- | :--- | :--- |
| 8-Lead <br> MSOP | 6-Lead <br> SOT-23 | 5-Lead <br> SOT-23 | Mnemonic | Description |
| 1 | 1 | 1 | D | Drain Terminal. Can be an input or output. |
| $2,3,5$ | 5 |  | NC | No Connect |
| 4 | 6 | 5 | VDD | Most Positive Power Supply Potential. |
| 6 | 4 | 4 | IN | Logic Control Input. |
| 7 | 3 | 3 | GND | Ground (0 V) Reference. |
| 8 | 2 | 2 | S | Source Terminal. Can be an input or output. |

## TYPICAL PERFORMANCE CHARACTERISTICS



Figure 5. On Resistance as a Function of $V_{D}\left(V_{S}\right)$ Single Supplies


Figure 6. On Resistance as a Function of $V_{D}\left(V_{s}\right)$ for Different Temperatures $V_{D D}=3 \mathrm{~V}$


Figure 7. On Resistance as a Function of $V_{D}\left(V_{S}\right)$ for Different Temperatures $V_{D D}=5 \mathrm{~V}$


Figure 8. Supply Current vs. Input Switching Frequency


Figure 9. Off Isolation vs. Frequency


Figure 10. Bandwidth

## ADG701/ADG702

## TERMINOLOGY

Table 7.

| Term | Description |
| :---: | :---: |
| Ron | Ohmic resistance between D and S. |
| Rflation) | Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range. |
| Is (OFF) | Source leakage current with the switch off. |
| ID (OFF) | Drain leakage current with the switch off. |
| $\mathrm{l}_{\mathrm{D}}, \mathrm{I}_{\mathrm{S}}(\mathrm{ON})$ | Channel leakage current with the switch on. |
| $\mathrm{V}_{\mathrm{D}}$ (VS) | Analog voltage on terminals D and S . |
| $\mathrm{C}_{\text {S }}$ (OFF) | Off switch source capacitance. |
| $\mathrm{C}_{\mathrm{D}}$ (OFF) | Off switch drain capacitance. |
| $\mathrm{C}_{\mathrm{D}}, \mathrm{C}_{S}(\mathrm{ON})$ | On switch capacitance. |
| ton | Delay between applying the digital control input and the output switching on. See Figure 14. |
| toff | Delay between applying the digital control input and the output switching off. |
| Off Isolation | A measure of unwanted signal coupling through an off switch. |
| Charge Injection | A measure of the glitch impulse transferred from the digital input to the analog output during switching. |
| Bandwidth | The frequency at which the output is attenuated by -3 dB . |
| On Response | The frequency response of the on switch. |
| On Loss | The voltage drop across the on switch seen in Figure 10 as the number of decibels that the signal is from 0 dB at very low frequencies. |

## TEST CIRCUITS



Figure 14. Switching Times


Figure 15. Charge Injection


Figure 16. Off Isolation


## ADG701/ADG702

## APPLICATIONS INFORMATION

The ADG701/ADG702 belong to the Analog Devices family of CMOS switches. This series of general-purpose switches has improved switching times, lower on resistance, higher bandwidth, low power consumption, and low leakage currents.

## ADG701/ADG702 SUPPLY VOLTAGES

Functionality of the ADG701/ADG702 extends from 1.8 V to 5.5 V single supply, making the parts ideal for battery-powered instruments, where power efficiency and performance are important design parameters.

It is important to note that the supply voltage affects the input signal range, on resistance, and switching times of the part. The effects of the power supplies can be clearly seen in the Typical Performance Characteristics and the Specifications sections.

For $\mathrm{V}_{\mathrm{DD}}=1.8 \mathrm{~V}$ operation, Ron is typically $40 \Omega$ over the temperature range.

## BANDWIDTH

Figure 18 illustrates the parasitic components that affect the ac performance of CMOS switches (a box surrounds the switch). Additional external capacitances further degrade performance by affecting feedthrough, crosstalk, and system bandwidth.


Figure 18. Switch Represented by Equivalent Parasitic Components
The transfer function that describes the equivalent diagram of the switch (see Figure 18) is of the form (A)s, shown in the following equation:

$$
A(s)=R_{T}\left[\frac{s\left(R_{O N} C_{D S}\right)+1}{s\left(R_{O N} C_{T} R_{T}\right)+1}\right]
$$

where $C_{T}=C_{L O A D}+C_{D}+C_{D S}$.

The signal transfer characteristic is dependent on the switch channel capacitance, $\mathrm{C}_{\mathrm{Ds}}$. This capacitance creates a frequency zero in the numerator of the transfer function $\mathrm{A}(\mathrm{s})$. Because the switch on resistance is small, this zero usually occurs at high frequencies. The bandwidth is a function of the switch output capacitance combined with $\mathrm{C}_{\mathrm{Ds}}$ and the load capacitance. The frequency pole corresponding to these capacitances appears in the denominator of $\mathrm{A}(\mathrm{s})$.

The dominant effect of the output capacitance, $C_{D}$, causes the pole breakpoint frequency to occur first. To maximize bandwidth, a switch must have a low input and output capacitance and low on resistance. The on response vs. frequency for the ADG701/ ADG702 can be seen in Figure 10.

## OFF ISOLATION

Off isolation is a measure of the input signal coupled through an off switch to the switch output. The capacitance, $\mathrm{C}_{\mathrm{DS}}$, couples the input signal to the output load when the switch is off, as shown in Figure 19.


Figure 19. Off Isolation Is Affected by External Load Resistance and Capacitance

The larger the value of $C_{D S}$, the larger the values of feedthrough produced. Figure 9 illustrates the drop in off isolation as a function of frequency. From dc to roughly 1 MHz , the switch shows better than -75 dB isolation. Up to frequencies of 10 MHz , the off isolation remains better than -55 dB . As the frequency increases, more of the input signal is coupled through to the output. Off isolation can be maximized by choosing a switch with the smallest $C_{D S}$ possible. The values of load resistance and capacitance also affect off isolation, because they contribute to the coefficients of the poles and zeros in the transfer function of the switch when open.

$$
A(s)=R_{T}\left[\frac{s\left(R_{L O A D} C_{D S}\right)+1}{s\left(R_{L O A D}\right)\left(C_{T}\right)+1}\right]
$$

## OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-187-AA
Figure 20. 8-Lead Mini Small Outline Package [MSOP] (RM-8)
Dimensions shown in millimeters


Figure 21. 6-Lead Small Outline Transistor Package [SOT-23] (RT-6)
Dimensions shown in millimeters

## ADG701/ADG702



COMPLIANT TO JEDEC STANDARDS MO-178-AA
Figure 22. 5-Lead Small Outline Transistor Package [SOT-23]
(RJ-5)
Dimensions shown in millimeters
ORDERING GUIDE

| Model | Package Description | Package Option | Branding |
| :---: | :---: | :---: | :---: |
| ADG701BRJ-500RL7 | 5-Lead Small Outline Transistor Package [SOT-23] | RJ-5 | S3B |
| ADG701BRJ-REEL | 5-Lead Small Outline Transistor Package [SOT-23] | RJ-5 | S3B |
| ADG701BRJ-REEL7 | 5-Lead Small Outline Transistor Package [SOT-23] | RJ-5 | S3B |
| ADG701BRM | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | S3B |
| ADG701BRM-REEL | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | S3B |
| ADG701BRM-REEL7 | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | S3B |
| ADG701BRT-REEL | 6-Lead Small Outline Transistor Package [SOT-23] | RT-6 | S3B |
| ADG701BRT-REEL7 | 6-Lead Small Outline Transistor Package [SOT-23] | RT-6 | S3B |
| ADG701BRJZ-500RL7 ${ }^{1}$ | 5-Lead Small Outline Transistor Package [SOT-23] | RJ-5 | S3B\# |
| ADG701BRJZ-REEL ${ }^{1}$ | 5-Lead Small Outline Transistor Package [SOT-23] | RJ-5 | S3B\# |
| ADG701BRJZ-REEL7 ${ }^{1}$ | 5-Lead Small Outline Transistor Package [SOT-23] | RJ-5 | S3B\# |
| ADG701BRMZ ${ }^{1}$ | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | SOS |
| ADG701BRMZ-REEL71 ${ }^{1}$ | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | SOS |
| ADG701BRTZ-REEL ${ }^{1}$ | 6-Lead Small Outline Transistor Package [SOT-23] | RT-6 | S3B\# |
| ADG701BRTZ-REEL7 ${ }^{1}$ | 6-Lead Small Outline Transistor Package [SOT-23] | RT-6 | S3B\# |
| ADG702BRJ-500RL7 | 5-Lead Small Outline Transistor Package [SOT-23] | RJ-5 | S4B |
| ADG702BRJ-REEL | 5-Lead Small Outline Transistor Package [SOT-23] | RJ-5 | S4B |
| ADG702BRJ-REEL7 | 5-Lead Small Outline Transistor Package [SOT-23] | RJ-5 | S4B |
| ADG702BRM | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | S4B |
| ADG702BRM-REEL | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | S4B |
| ADG702BRM-REEL7 | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | S4B |
| ADG702BRT-REEL | 6-Lead Small Outline Transistor Package [SOT-23] | RT-6 | S4B |
| ADG702BRT-REEL7 | 6-Lead Small Outline Transistor Package [SOT-23] | RT-6 | S4B |
| ADG702BRJZ-500RL7 ${ }^{1}$ | 5-Lead Small Outline Transistor Package [SOT-23] | RJ-5 | S14 |
| ADG702BRJZ-REEL ${ }^{1}$ | 5-Lead Small Outline Transistor Package [SOT-23] | RJ-5 | S14 |
| ADG702BRJZ-REEL7 ${ }^{1}$ | 5-Lead Small Outline Transistor Package [SOT-23] | RJ-5 | S14 |
| ADG702BRMZ ${ }^{1}$ | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | S14 |
| ADG702BRMZ-REEL7 ${ }^{1}$ | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | S14 |
| ADG702BRTZ-REEL ${ }^{1}$ | 6-Lead Small Outline Transistor Package [SOT-23] | RT-6 | S4B\# |
| ADG702BRTZ-REEL7 ${ }^{1}$ | 6-Lead Small Outline Transistor Package [SOT-23] | RT-6 | S4B\# |

${ }^{1} \mathrm{Z}=\mathrm{Pb}$-free part, \# denotes lead-free product, may be top or bottom marked.
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## X-ON Electronics

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HMC444LP4ETR LTC1564CG\#PBF HMC505LP4ETR 5962-8686101XA 5962-89710013X 5962-9169003MXA 5962-9176404M3A 5962-
9316401MXA 5962-9452101M2A EV1HMC1160LP5 EV1HMC305SLP4 EV1HMC306AMS10 EV1HMC557ALC4 EV1HMC6146BLC5A
EV1HMC6832ALP5L EV1HMC7912LP5 EV1HMC7992LP3D EV1HMC951BLP4 EV-AD5443/46/53SDZ EV-ADF70301-433AZ EV-
ADF70301-868BZ EV-ADUCM322IQSPZ EV-ADUCM322QSPZ EVAL01-HMC1048LC3B EVAL01-HMC1055LP2C EVAL01-
HMC1063LP3 EVAL01-HMC197B EVAL01-HMC760LC4B EVAL01-HMC829LP6GE EVAL01-HMC833LP6GE EVAL01-
HMC835LP6G EVAL01-HMC985LP4KE EVAL01-HMC987LP5E EVAL01-HMC988LP3E EVAL01-HMC995LP5GE EVAL02-
HMC1034LP6G EVAL-3CH4CHSOICEBZ EVAL-AD1871EBZ EVAL-AD5063EBZ EVAL-AD5064EBZ EVAL-AD5171DBZ


[^0]:    ${ }^{1}$ Guaranteed by design, not subject to production test.

[^1]:    ${ }^{1}$ Guaranteed by design, not subject to production test.

[^2]:    ${ }^{1}$ Overvoltages at $\mathrm{IN}, \mathrm{S}$, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

